Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HA06

APPLICATIONS

General Purpose Amplifier.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……625mW

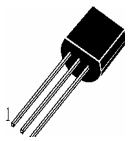
V_{CBO}——Collector-Base Voltage……80V

V_{CEO}——Collector-Emitter Voltage……80V

V_{EBO}——Emitter-Base Voltage……4V

I_C——Collector Current……500mA

TO-92



1－Emitter，E
2－Base，B
3－Collector，C

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CEO}	Collector-Emitter Breakdown Voltage	80			V	I_C=1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	4			V	I_E=100μA，I_C=0
H_{FE}（1）	DC Current Gain	50				V_{CE}=1V, I_C=10mA
H_{FE}（2）	DC Current Gain	50				V_{CE}=1V, I_C=100mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.25	V	I_C=100mA, I_B=10mA
V_{BE}（on）	Base-Emitter On Voltage			1.2	V	V_{CE}=1V, I_C=100mA
I_{CBO}	Collector Cut-off Current			100	nA	V_{CB}=80V, I_E=0
I_{CEO}	Collector Cut-off Current			100	nA	V_{CE}=60V, I_B=0
f_T	Current Gain-Bandwidth Product	100			MHz	V_{CE}=20V,I_C=10mA, f=100MHz